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Effects of structural imperfection on the electronic properties of graphene/WSe_2 heterostructures

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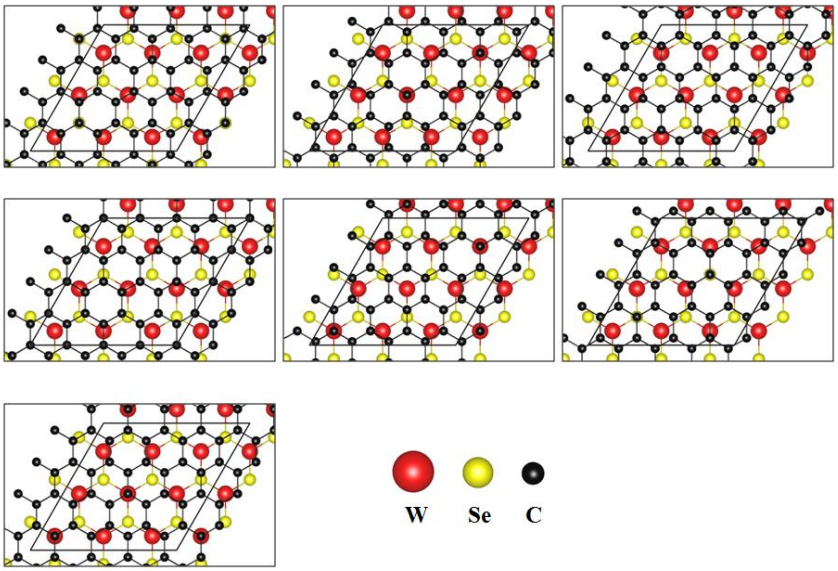

Fig. S1 Representative configurations of G/WSe_2 vdW heterojunctions in seven different stacking patterns.

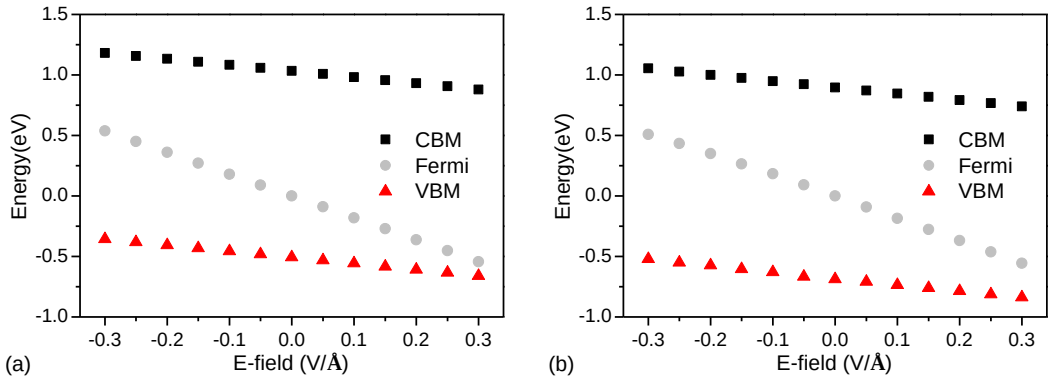

Fig. S2 Change of band offset of the (a) G/WSe_2 and (b) G/WSe_2-$V_{di\text{-}Se}$ vdW heterostructures under the electric field. The zero energies of the G/WSe_2 and G/WSe_2-$V_{di\text{-}Se}$ vdW heterostructures are separately referenced to the VBM of their most stable configurations at zero field.